

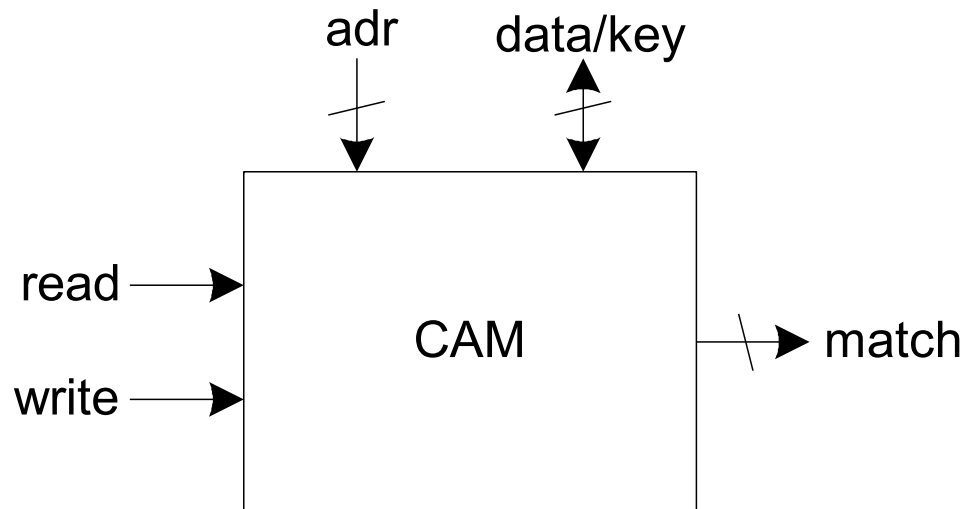
Lecture 16: CAMs, ROMs, PLAs

Outline

- ❑ Content-Addressable Memories
- ❑ Read-Only Memories
- ❑ Programmable Logic Arrays

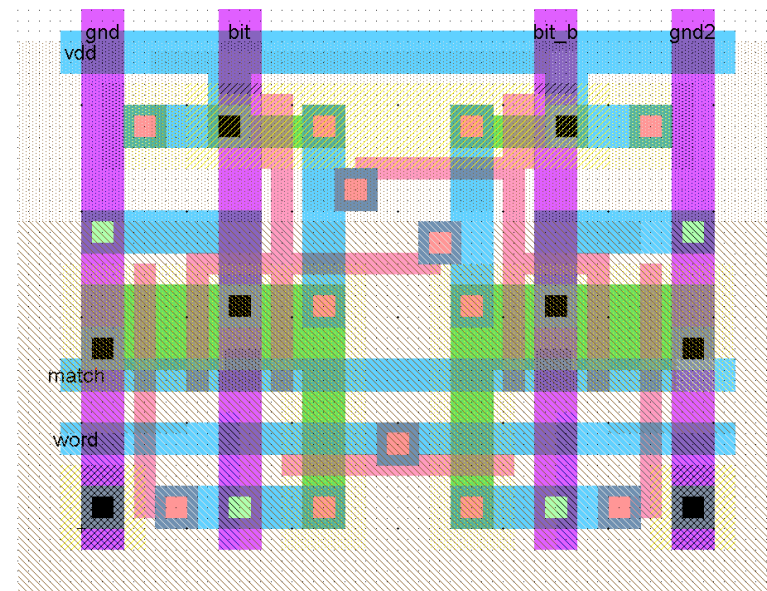
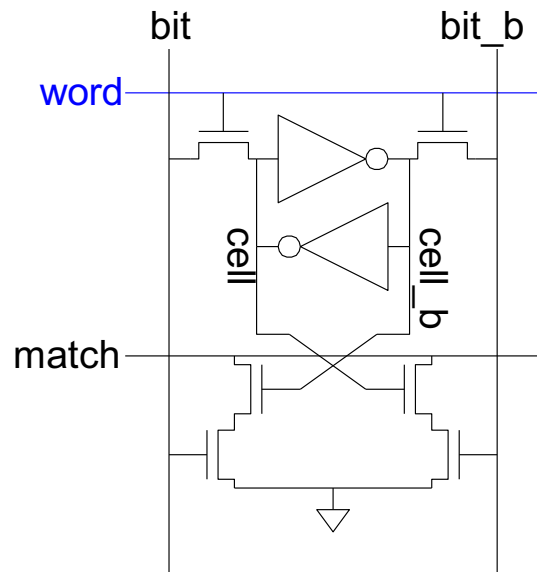
CAMs

- ❑ Extension of ordinary memory (e.g. SRAM)
 - Read and write memory as usual
 - Also *match* to see which words contain a *key*



10T CAM Cell

- Add four match transistors to 6T SRAM
 - 56 x 43 λ unit cell



CAM Cell Operation

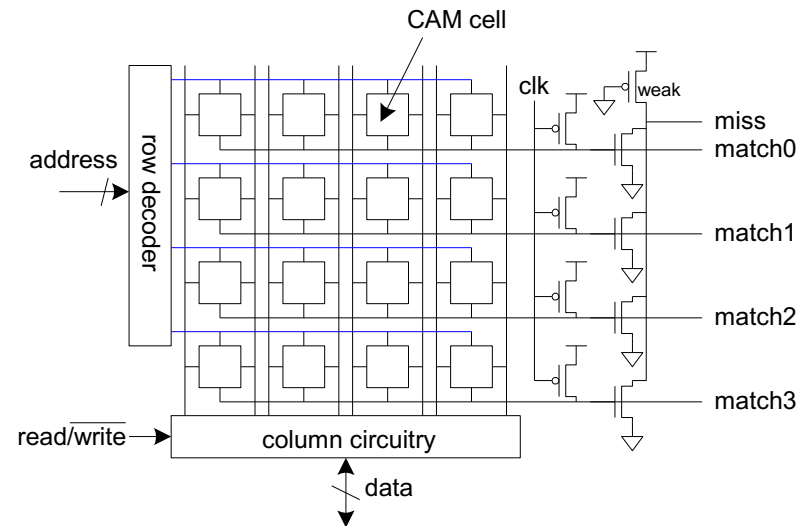
❑ Read and write like ordinary SRAM

❑ For matching:

- Leave wordline low
- Precharge matchlines
- Place key on bitlines
- Matchlines evaluate

❑ Miss line

- Pseudo-nMOS NOR of match lines
- Goes high if no words match



Read-Only Memories

- ❑ Read-Only Memories are nonvolatile
 - Retain their contents when power is removed
- ❑ Mask-programmed ROMs use one transistor per bit
 - Presence or absence determines 1 or 0

ROM Example

❑ 4-word x 6-bit ROM

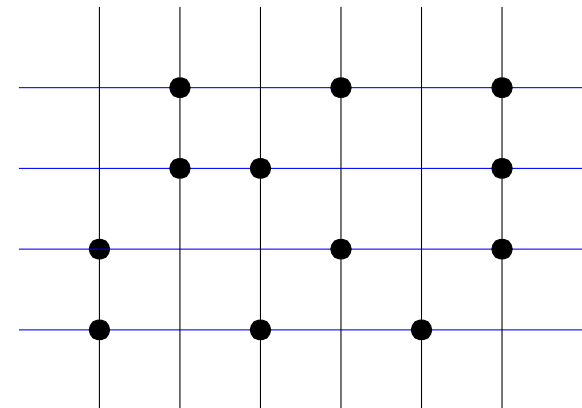
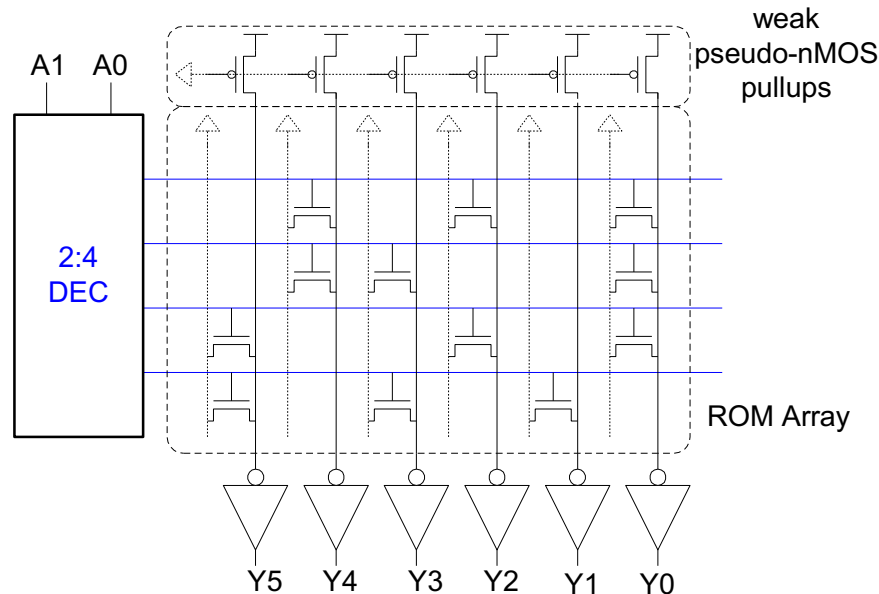
- Represented with dot diagram
- Dots indicate 1's in ROM

Word 0: 010101

Word 1: 011001

Word 2: 100101

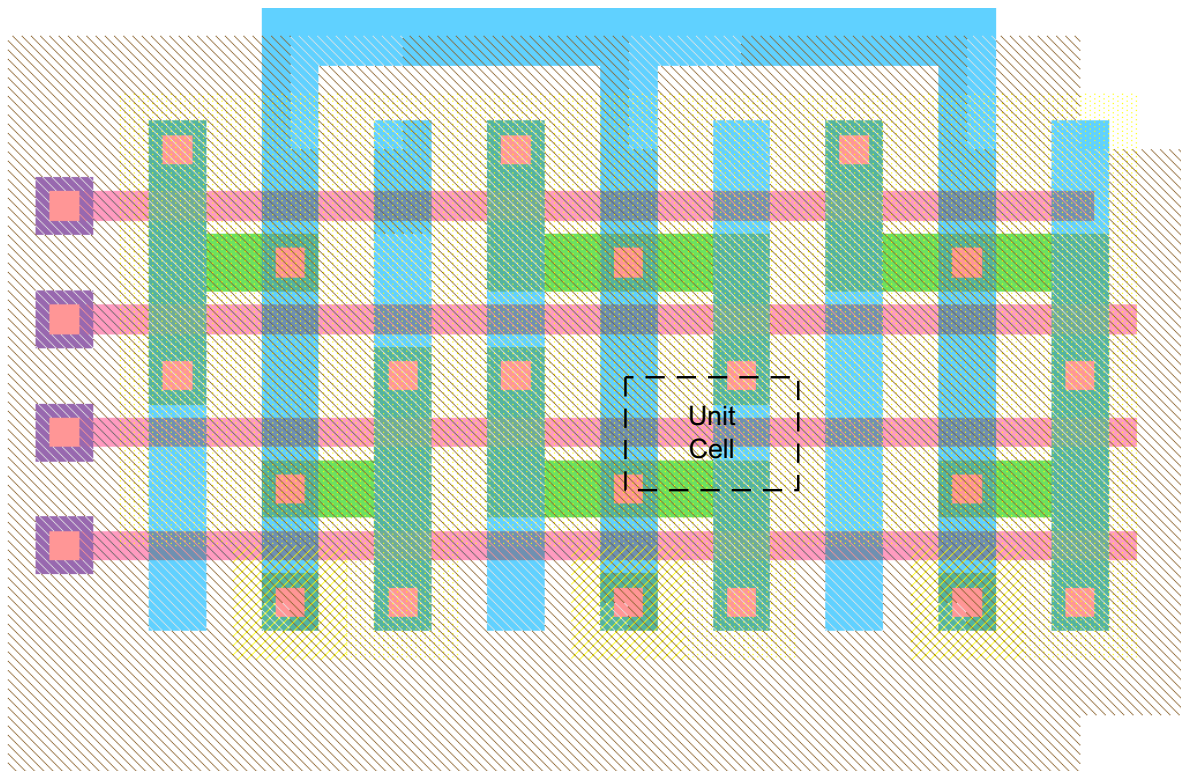
Word 3: 101010



Looks like 6 4-input pseudo-nMOS NORs

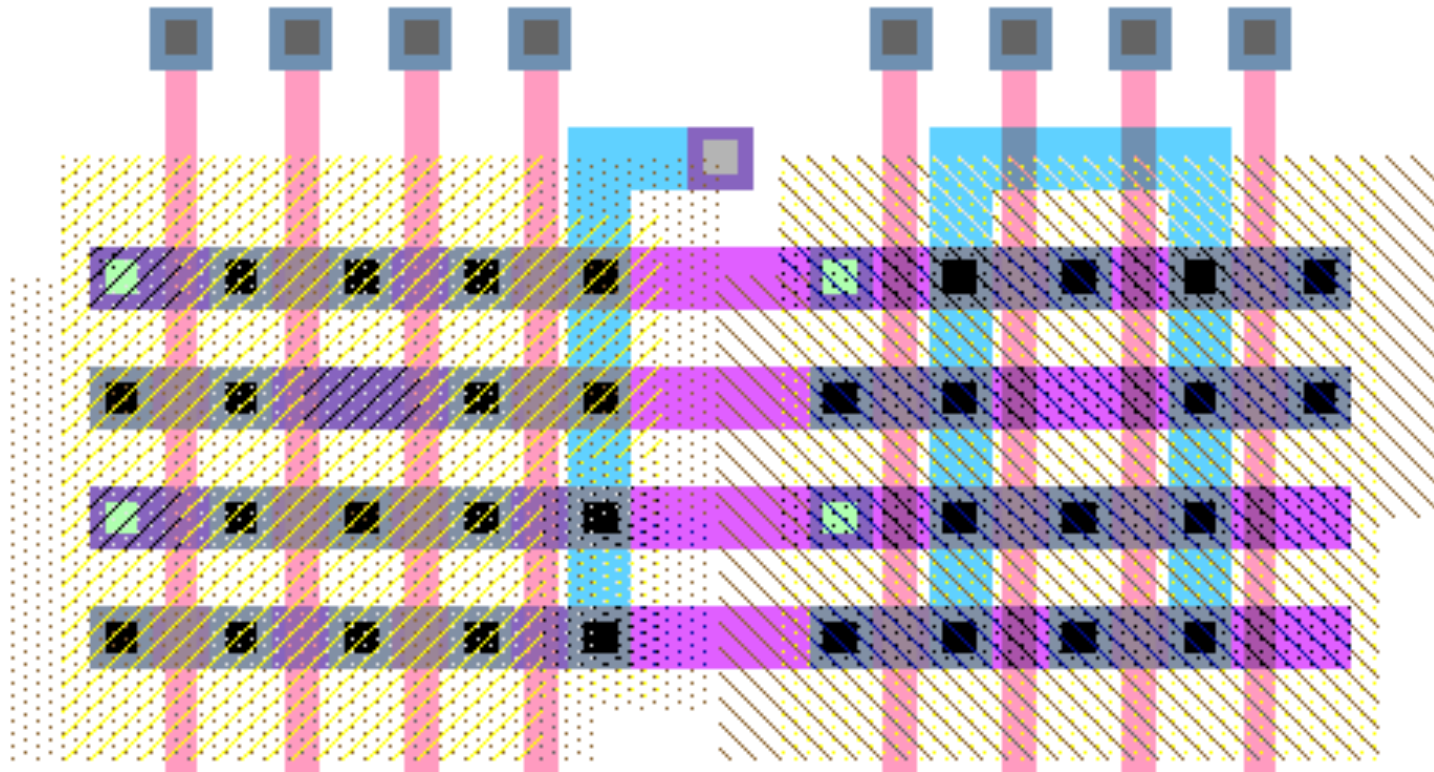
ROM Array Layout

- Unit cell is $12 \times 8 \lambda$ (about 1/10 size of SRAM)

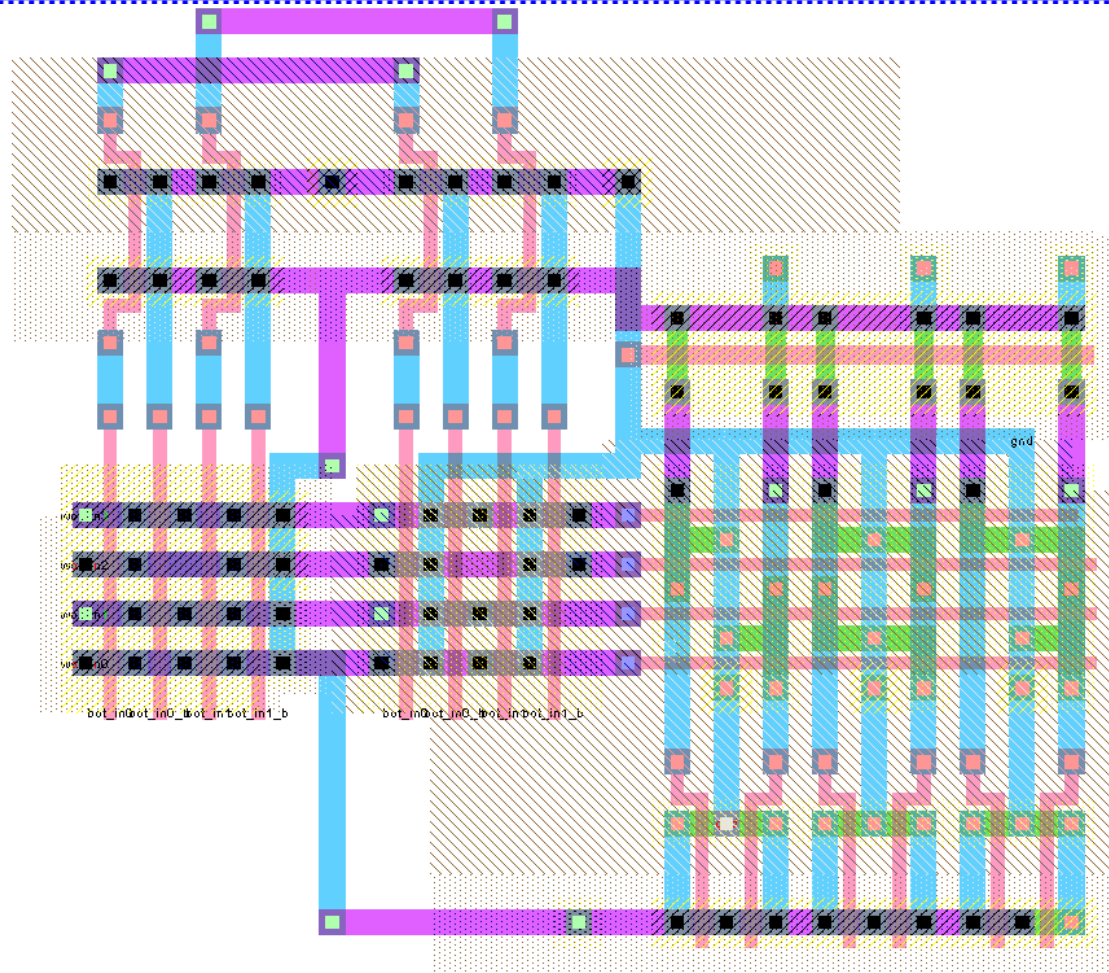


Row Decoders

- ❑ ROM row decoders must pitch-match with ROM
 - Only a single track per word!



Complete ROM Layout



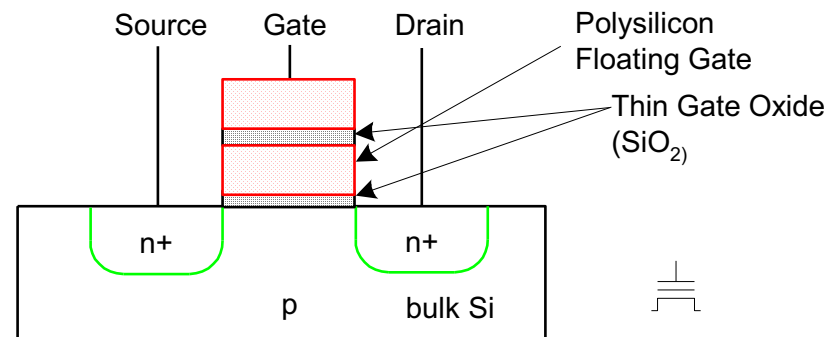
PROMs and EPROMs

❑ Programmable ROMs

- Build array with transistors at every site
- Burn out fuses to disable unwanted transistors

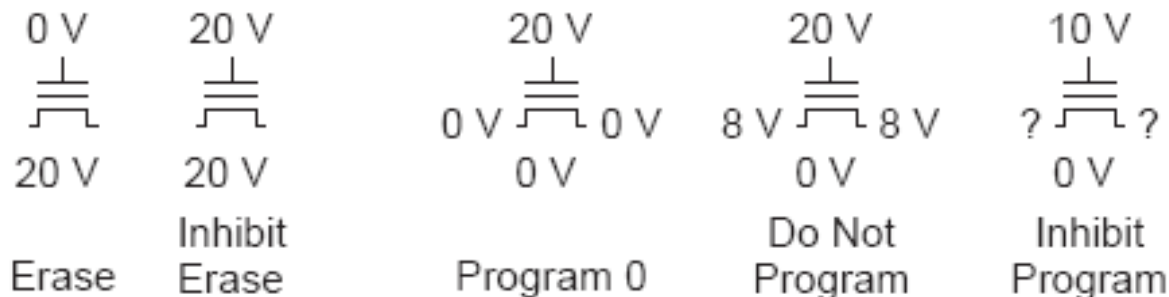
❑ Electrically Programmable ROMs

- Use floating gate to turn off unwanted transistors
- EPROM, EEPROM, Flash



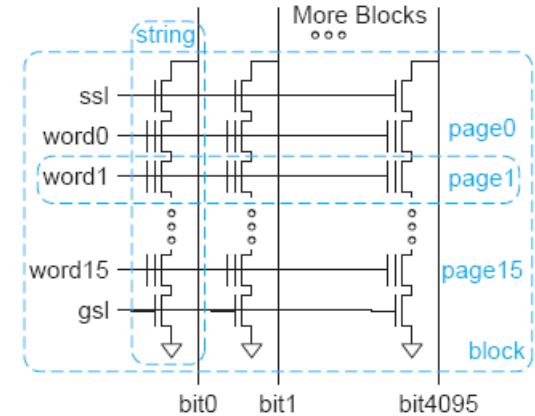
Flash Programming

- ❑ Charge on floating gate determines V_t
- ❑ Logic 1: negative V_t
- ❑ Logic 0: positive V_t
- ❑ Cells erased to 1 by applying a high body voltage so that electrons tunnel off floating gate into substrate
- ❑ Programmed to 0 by applying high gate voltage



NAND Flash

- ❑ High density, low cost / bit
 - Programmed one page at a time
 - Erased one block at a time
- ❑ Example:
 - 4096-bit pages
 - 16 pages / 8 KB block
 - Many blocks / memory



64 Gb NAND Flash

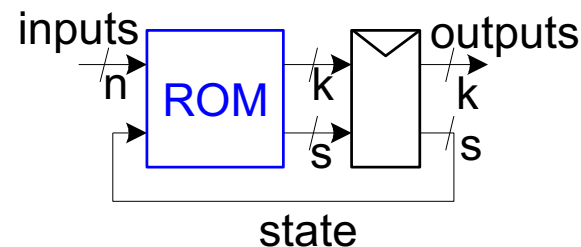
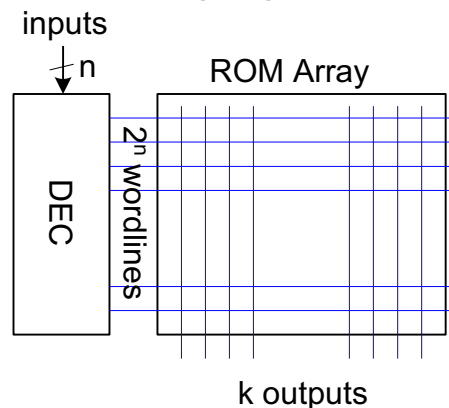
- ❑ 64K cells / page
- ❑ 4 bits / cell (multiple V_t)
- ❑ 64 cells / string
 - 256 pages / block
- ❑ 2K blocks / plane
- ❑ 2 planes



[Trinh09]

Building Logic with ROMs

- ❑ Use ROM as lookup table containing truth table
 - n inputs, k outputs requires 2^n words x k bits
 - Changing function is easy – reprogram ROM
- ❑ Finite State Machine
 - n inputs, k outputs, s bits of state
 - Build with 2^n bit ROM and s bit reg



Example: RoboAnt

Let's build an Ant

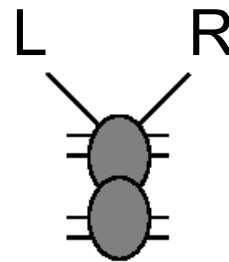
Sensors: Antennae

(L,R) – 1 when in contact

Actuators: Legs

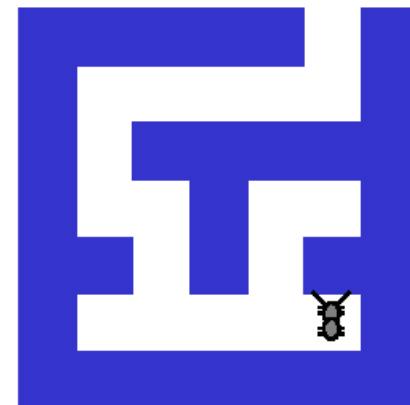
Forward step F

Ten degree turns TL, TR



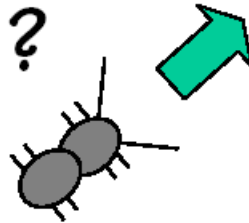
Goal: make our ant smart enough to get out of a maze

Strategy: keep right antenna on wall

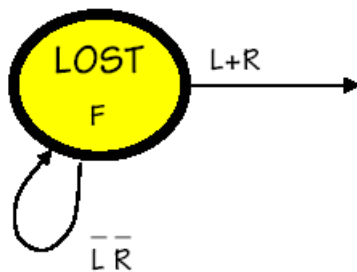


(RoboAnt adapted from MIT 6.004 2002 OpenCourseWare by Ward and Terman)

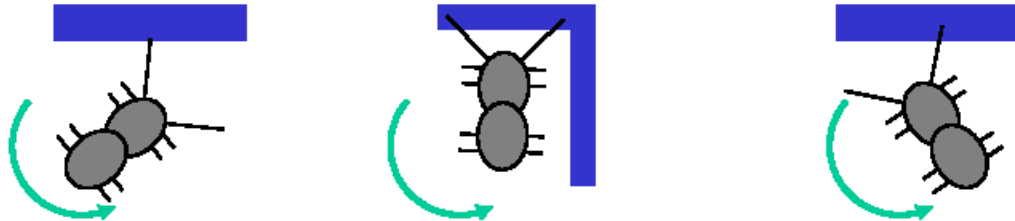
Lost in space



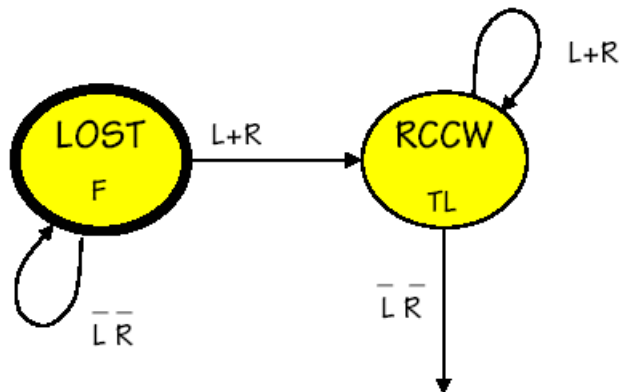
- ❑ Action: go forward until we hit something
 - Initial state



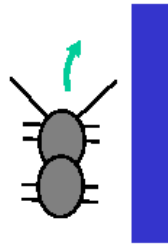
Bonk!!!



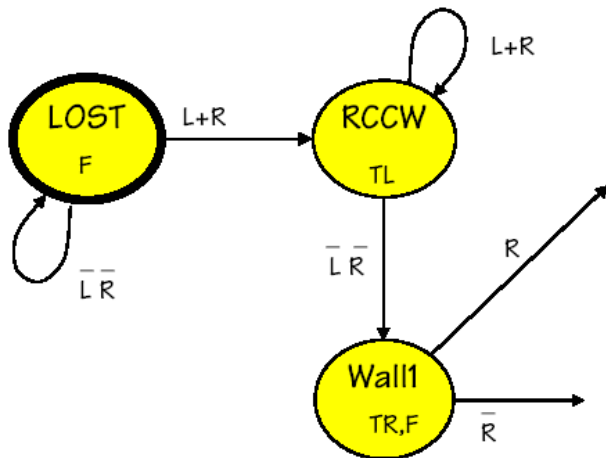
- ❑ Action: turn left (rotate counterclockwise)
 - Until we don't touch anymore



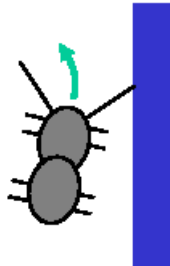
A little to the right



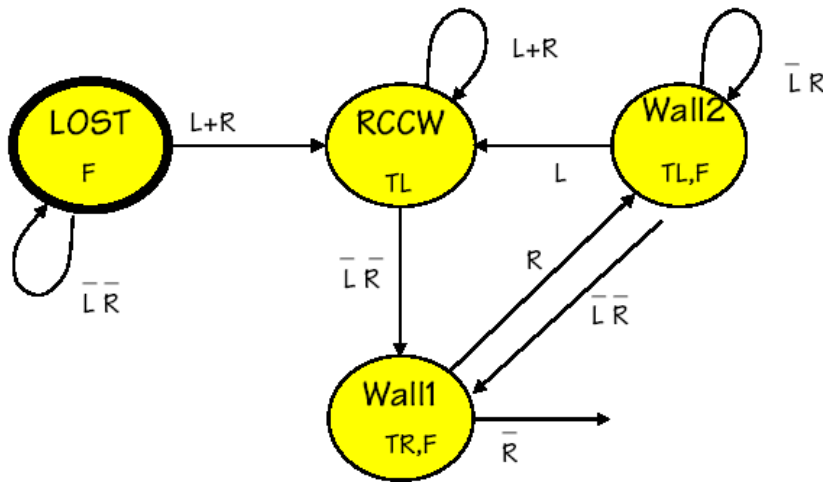
- Action: step forward and turn right a little
 - Looking for wall



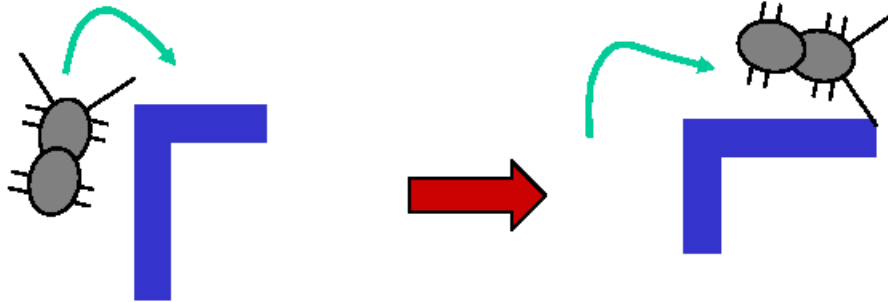
Then a little to the left



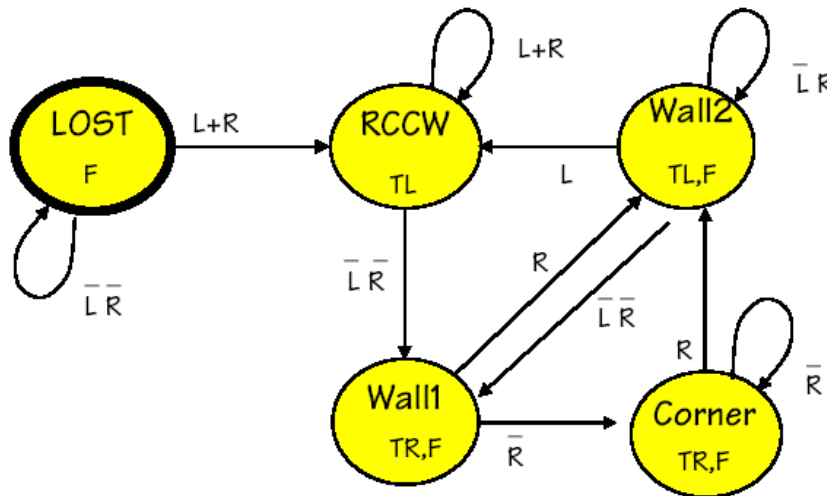
- Action: step and turn left a little, until not touching



Whoops – a corner!

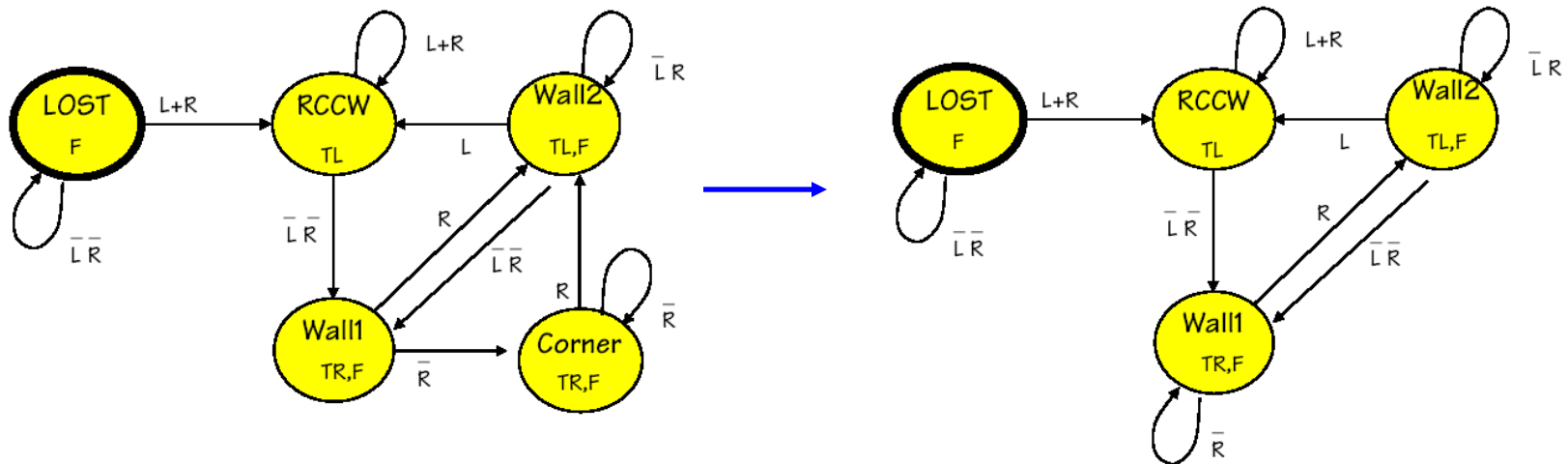


- Action: step and turn right until hitting next wall



Simplification

- ❑ Merge equivalent states where possible

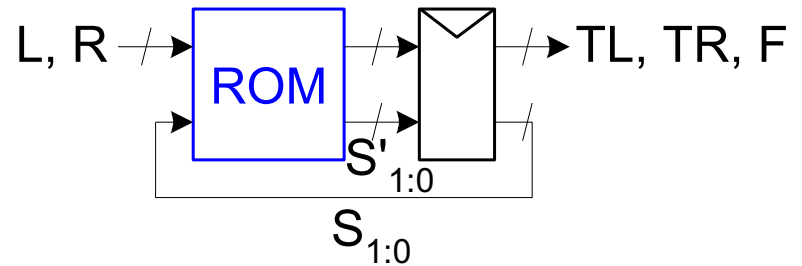
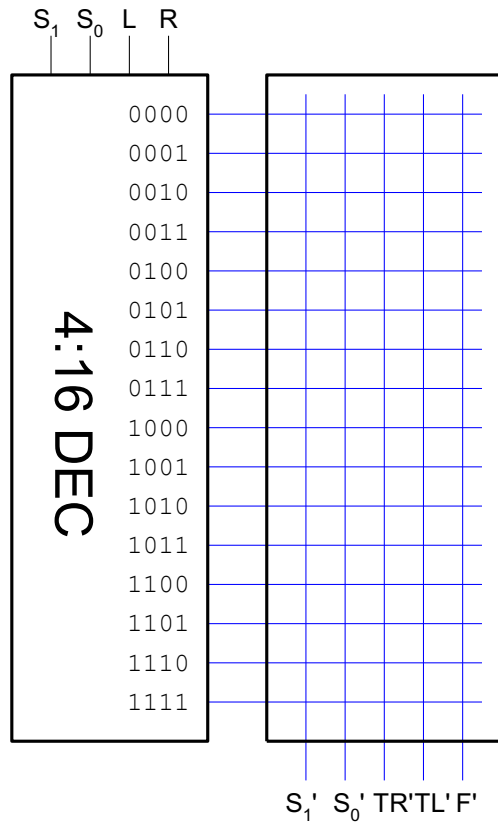


State Transition Table

	$S_{1:0}$	L	R	$S_{1:0}'$	TR	TL	F
Lost	00	0	0	00	0	0	1
	00	1	X	01	0	0	1
	00	0	1	01	0	0	1
RCCW	01	1	X	01	0	1	0
	01	0	1	01	0	1	0
	01	0	0	10	0	1	0
Wall1	10	X	0	10	1	0	1
	10	X	1	11	1	0	1
Wall2	11	1	X	01	0	1	1
	11	0	0	10	0	1	1
	11	0	1	11	0	1	1

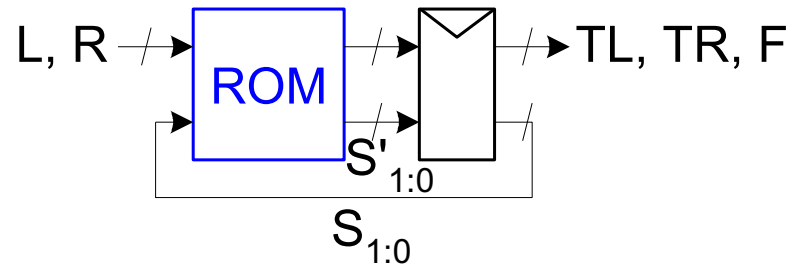
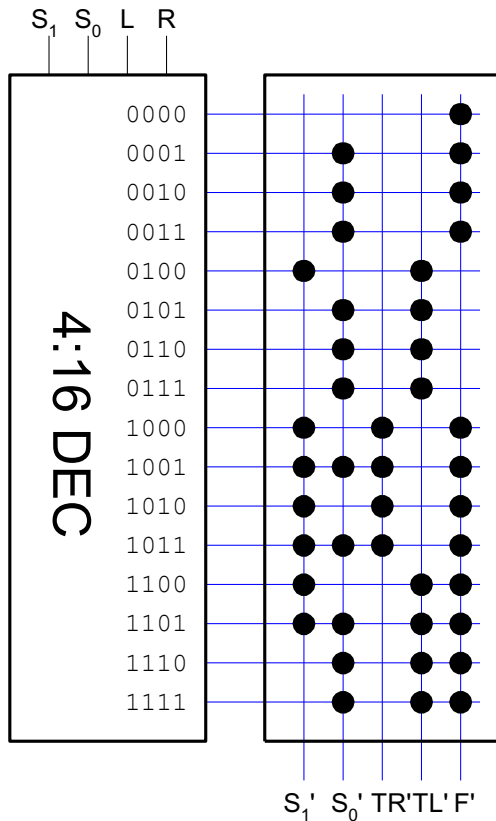
ROM Implementation

❑ 16-word x 5 bit ROM



ROM Implementation

□ 16-word x 5 bit ROM



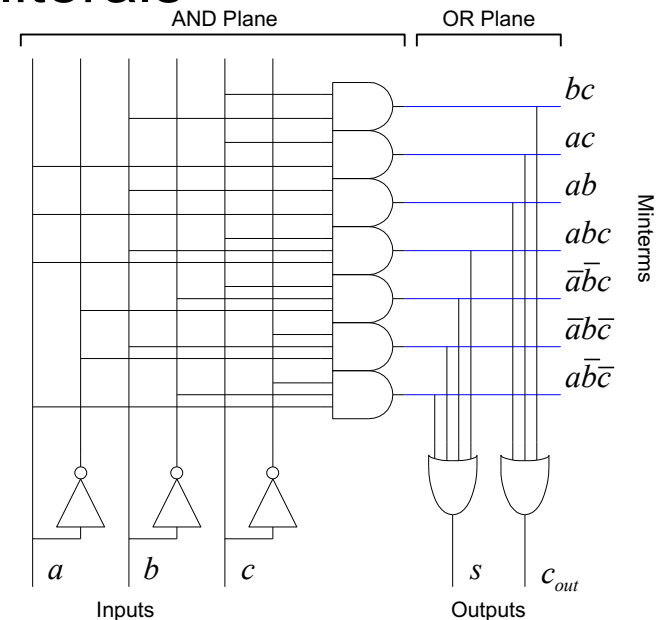
PLAs

- ❑ A *Programmable Logic Array* performs any function in sum-of-products form.
- ❑ *Literals*: inputs & complements
- ❑ *Products / Minterms*: AND of literals
- ❑ *Outputs*: OR of Minterms

- ❑ Example: Full Adder

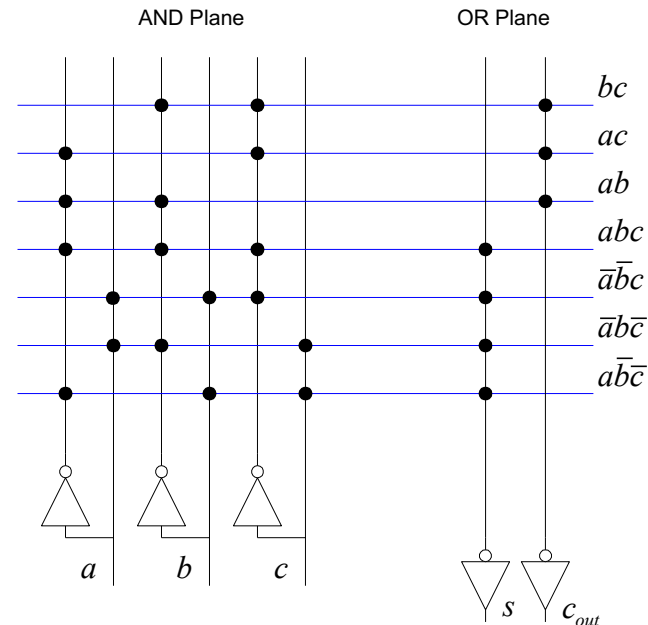
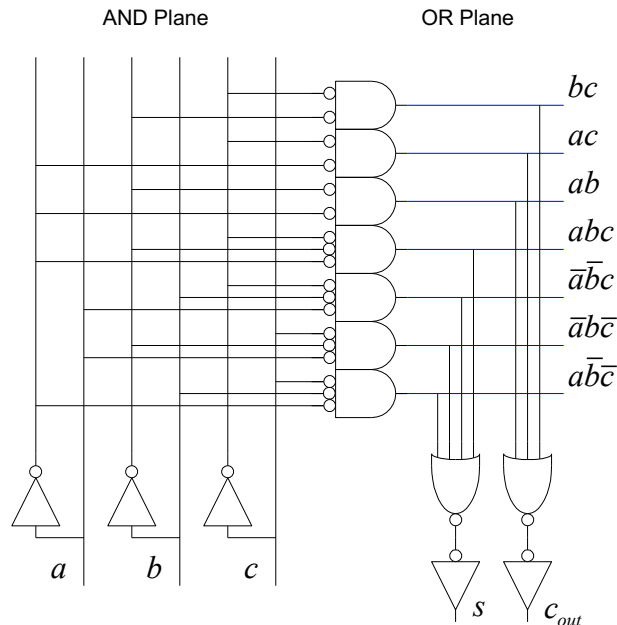
$$s = a\bar{b}\bar{c} + \bar{a}b\bar{c} + \bar{a}\bar{b}c + abc$$

$$c_{\text{out}} = ab + bc + ac$$

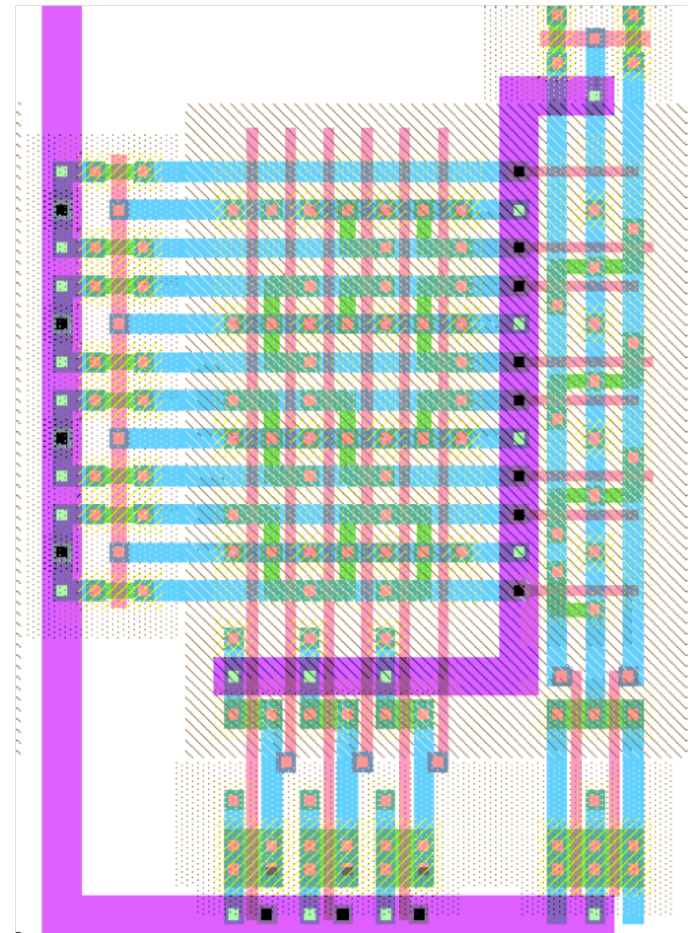
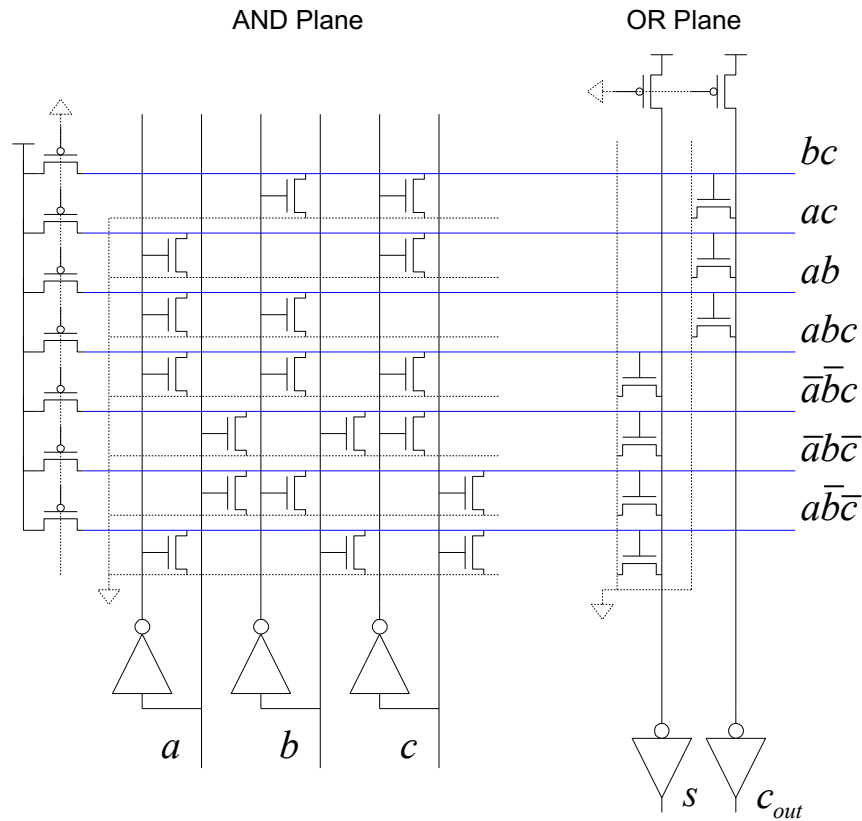


NOR-NOR PLAs

- ❑ ANDs and ORs are not very efficient in CMOS
- ❑ Dynamic or Pseudo-nMOS NORs are very efficient
- ❑ Use DeMorgan's Law to convert to all NORs



PLA Schematic & Layout



PLAs vs. ROMs

- ❑ The OR plane of the PLA is like the ROM array
- ❑ The AND plane of the PLA is like the ROM decoder
- ❑ PLAs are more flexible than ROMs
 - No need to have 2^n rows for n inputs
 - Only generate the minterms that are needed
 - Take advantage of logic simplification

Example: RoboAnt PLA

□ Convert state transition table to logic equations

$S_{1:0}$	L	R	$S_{1:0}'$	TR	TL	F
00	0	0	00	0	0	1
00	1	X	01	0	0	1
00	0	1	01	0	0	1
01	1	X	01	0	1	0
01	0	1	01	0	1	0
01	0	0	10	0	1	0
10	X	0	10	1	0	1
10	X	1	11	1	0	1
11	1	X	01	0	1	1
11	0	0	10	0	1	1
11	0	1	11	0	1	1

S_1'

	$S_1 S_0$			
	00	01	11	10
LR	00	0	1	1
	01	0	0	1
	11	0	0	0
	10	0	0	0

$$S_1' = S_1 \overline{S_0} + \overline{L} S_1 + \overline{L} R S_0$$

S_0'

	$S_1 S_0$			
	00	01	11	10
LR	00	0	0	0
	01	1	1	1
	11	1	1	1
	10	1	1	0

$$S_0' = R + L \overline{S_1} + L S_0$$

$$TR = S_1 \overline{S_0}$$

$$TL = S_0$$

$$F = S_1 + \overline{S_0}$$

RoboAnt Dot Diagram

$$S1' = S_1 \overline{S_0} + \overline{L} S_1 + \overline{L} \overline{R} S_0$$

$$S0' = R + L \overline{S_1} + L S_0$$

$$TR = S_1 \overline{S_0}$$

$$TL = S_0$$

$$F = S_1 + \overline{S_0}$$

